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FDA69N25 N-Channel UniFETTM MOSFET 250 V, 69 A, 41 mΩ

Features

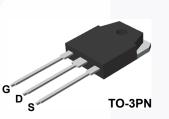
- + $R_{DS(on)}$ = 34 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 34.5 A
- Low Gate Charge (Typ. 77 nC)
- Low C_{rss} (Typ. 84 pF)

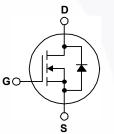
Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		FDA69N25	Unit	
V _{DSS}	Drain-Source Voltage	250	V	
V _{DS(Avalanche)}	Repetitive Avalanche Voltage	300	V	
ID	Drain Current	- Continuous (T _C = 25°C)	69	А
		- Continuous (T _C = 100°C)	44.2	Α
I _{DM}	Drain Current	- Pulsed (Note 1)	276	Α
V _{GSS}	Gate-Source Voltage	± 30	V	
E _{AS}	Single Pulsed Avalanche Ener	gy (Note 2)	1894	mJ
I _{AR}	Avalanche Current	(Note 1)	69	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		48	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P _D	Power Dissipation	$(T_{\rm C} = 25^{\circ}{\rm C})$	480	W
		- Derate above 25°C	3.84	W/°C
T _J , T _{STG}	Operating and Storage Temper	-55 to +150	°C	
ΤL	Maximum lead temperature for	300	°C	

Thermal Characteristics

Symbol	Parameter	FDA69N25	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.26	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/W	

June 2014

FDA69N25
- N-Channel
MOSFET

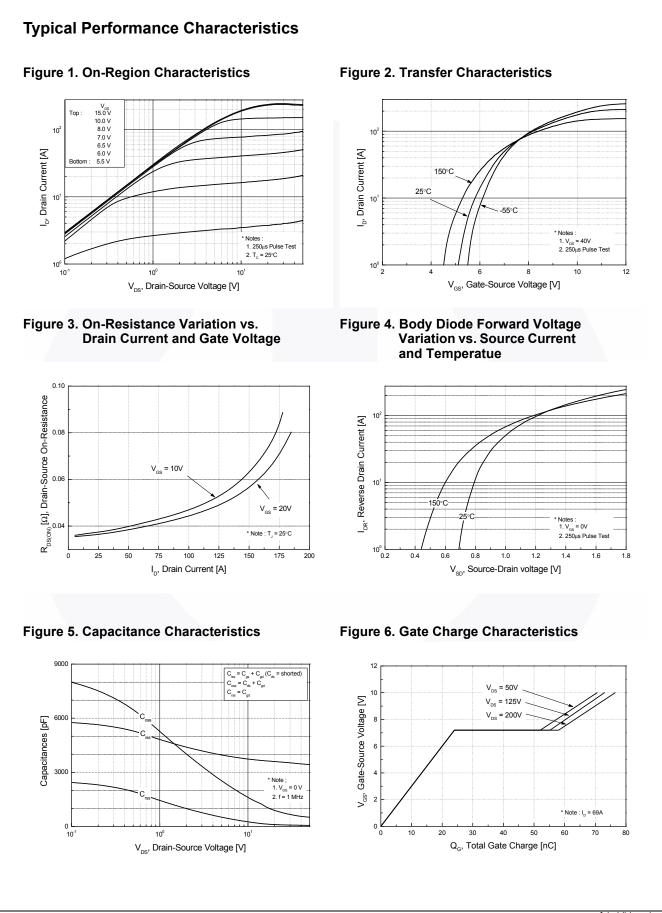
Part Number FDA69N25		Top Mark Pag		Packing Method	Reel Size	Tape Width		Qu	Quantity	
		FDA69N25	TO-3PN	Tube	N/A	N/A		30	30 units	
Electric	al Char	acteristics T _c =	25°C unless	otherwise noted.						
Symbol		Parameter		Test Conditio	ons	Min.	Тур.	Max.	Unit	
Off Charac	teristics									
BV _{DSS}	Drain-Source Breakdown Voltage			V_{GS} = 0 V, I _D = 250 μ A		250			V	
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient			I_D = 250 µA, Referenced to 25°C			0.25		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current			V _{DS} = 250 V, V _{GS} = 0 V				1	μA	
				V_{DS} = 200 V, T_{C} = 125°C				10	μA	
I _{GSSF}	Gate-Body Leakage Current, Forward		V _{GS} = 30 V, V _{DS} = 0 V				100	nA		
I _{GSSR}	Gate-Body	Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$		1			-100	nA		
On Charac	teristics									
V _{GS(th)}	Gate Three	shold Voltage		V_{DS} = V_{GS} , I_D = 250 μ	٩	3.0		5.0	V	
R _{DS(on)}	Static Drain	n-Source On-Resistanc	е	V_{GS} = 10 V, I _D = 34.5 A	4		0.034	0.041	Ω	
9 _{FS}	Forward Tr	ransconductance		V_{DS} = 40 V, I _D = 34.5 Å	A		25		S	
Dynamic C	haracterist	ics								
C _{iss}	Input Capa	acitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz			3570	4640	pF	
C _{oss}	Output Ca	pacitance					750	980	pF	
C _{rss}	Reverse T	ransfer Capacitance					84	130	pF	
Switching	Characteris	stics								
t _{d(on)}	Turn-On D	elay Time		V_{DD} = 125 V, I _D = 69 A, V_{GS} = 10 V, R _G = 25 Ω (Note 4)			95	200	ns	
t _r	Turn-On R	ise Time					855	1720	ns	
t _{d(off)}	Turn-Off D	elay Time					130	270	ns	
t _f	Turn-Off Fa	all Time					220	450	ns	
Qg	Total Gate	Charge		V_{DS} = 200 V, I _D = 69 A, V _{GS} = 10 V (Note 4)			77	100	nC	
Q _{gs}	Gate-Sour	ce Charge					24		nC	
Q _{gd}	Gate-Drain	n Charge					37		nC	
Drain-Sou	rce Diode C	haracteristics and Ma	ximum Rati	ngs			1			
I _S	Maximum Continuous Drain-Source Diode Forward Current						34	Α		
I _{SM}	Maximum Pulsed Drain-Source Diode Forward			I Current				136	Α	
V _{SD}	Drain-Sour	rce Diode Forward Volta	age	V _{GS} = 0 V, I _S = 69 A				1.4	V	
t _{rr}	Reverse R	ecovery Time		V _{GS} = 0 V, I _S = 69 A,			210		ns	
Q _{rr}	Reverse R	ecovery Charge		dl _F / dt = 100 A/µs			5.7		μC	

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.

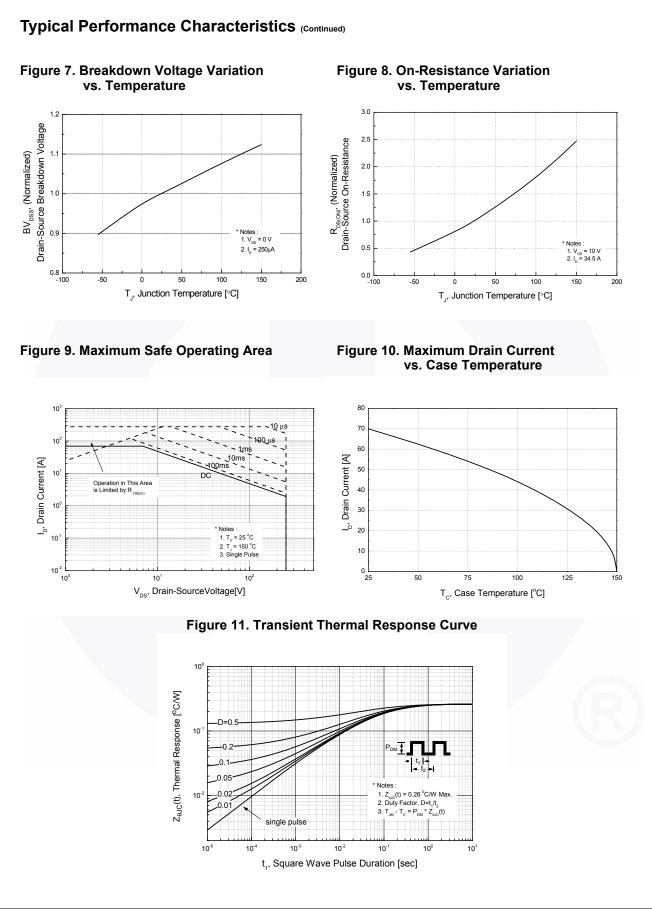
2. L = 0.64 mH, I_{AS} = 69 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} ≤ 69 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature typical characteristics.

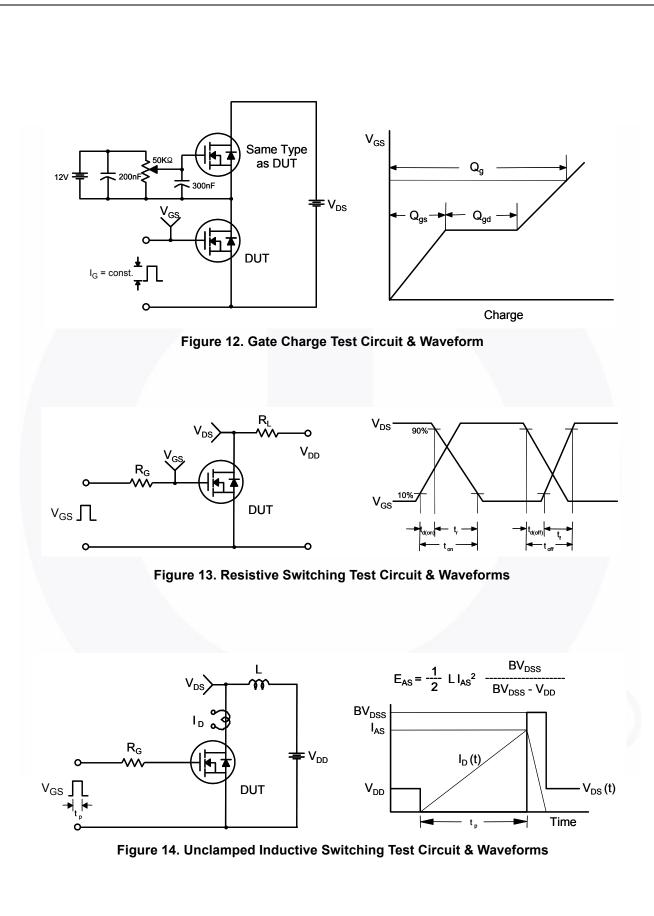
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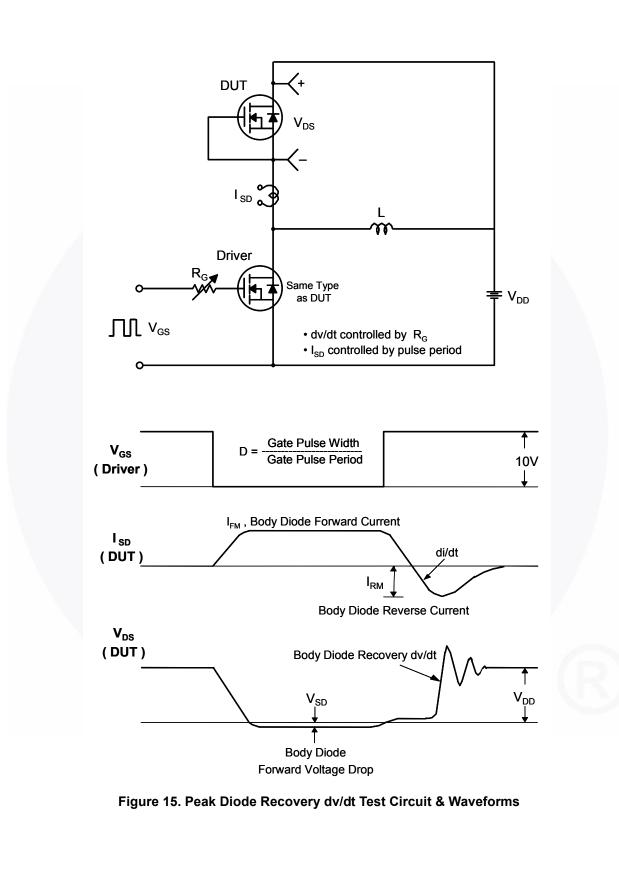
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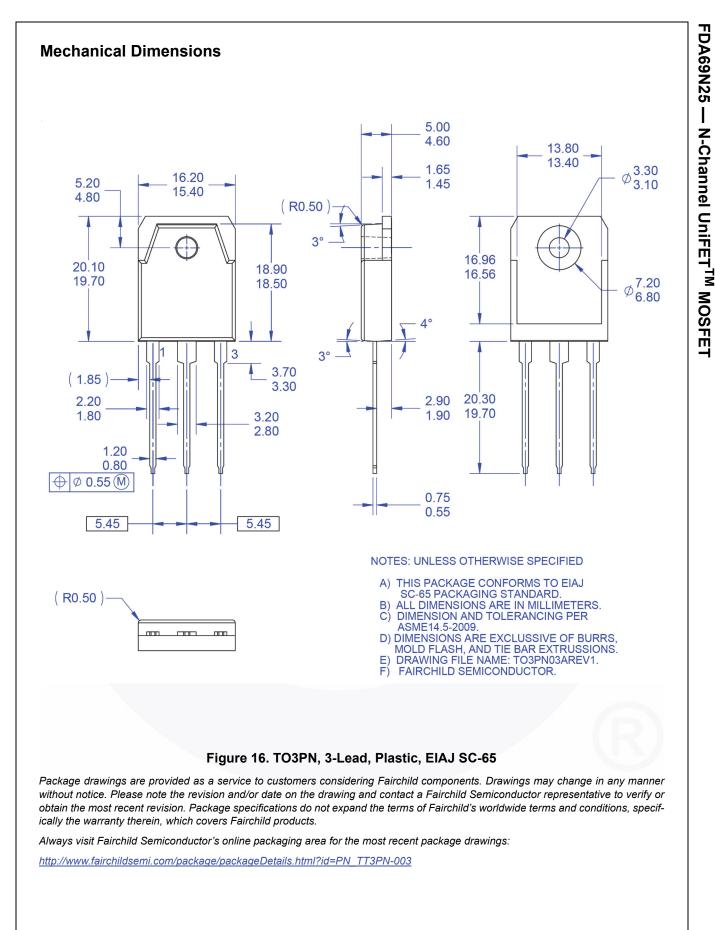




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No Identification Needed

Obsolete

Full Production

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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